NSN 5961-00-434-0160



Diode Semiconductor Device - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-00-434-0160 **Inclosure Material:** Glass **Overall Length:** Between 0.230 inches and 0.300 inches **Terminal Length:** Between 1.000 inches and 1.500 inches **Overall Diameter:** Between 0.085 inches and 0.107 inches **Mounting Method:** Terminal **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 70.0 working peak reverse voltage, peak total value **Current Rating Per Characteristic:** 10.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 400.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** 28.3 pf capacitance **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/383 government specification Shelf Life:

N/a **Unit Of Measure:**

Demilitarization:

No

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